T_C =25

Parameter	**Symbol**	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	$I_{D@}$TC=25	15	A
	$I_{D@}$TC=75	11	A
	$I_{D@}$TC=100	9.5	A
Pulsed Drain Current	I_{DM}	30	

Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	8	° C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	95	° C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	° C

Fig.1 Gate-Charge Characteristics

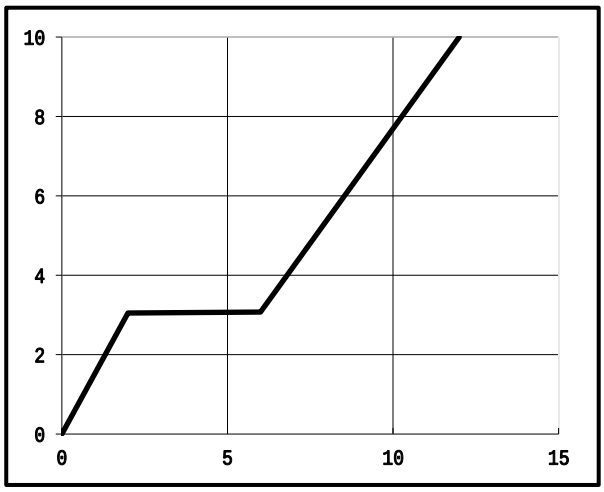

Fig.2 Capacitance Characteristics

Fig.3 Power Dissipation Derating Curve

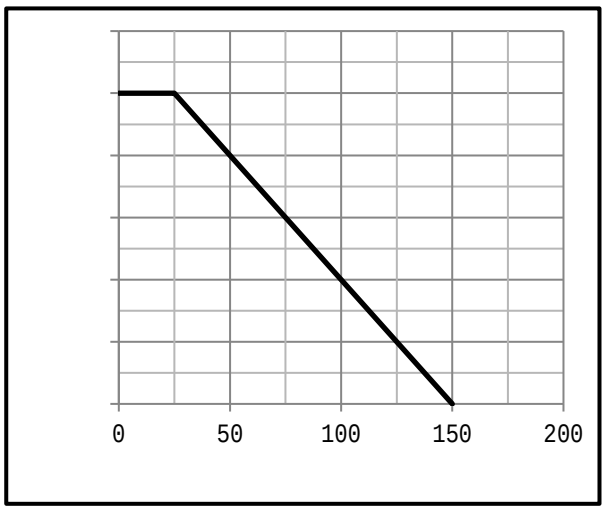

Fig.4 Typical output Characteristics

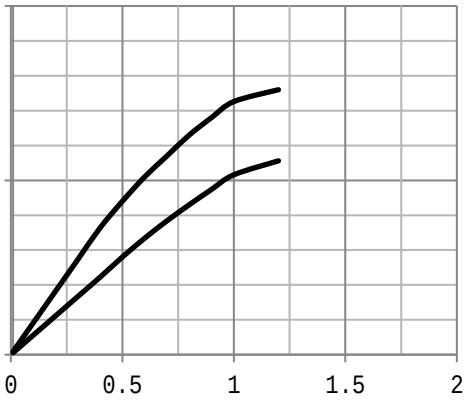

Fig.5 Threshold Voltage V.S Junction Temperature

Fig.6 Resistance V.S Drain Current

Fig.7 On-Resistance VS Gate Source Voltage

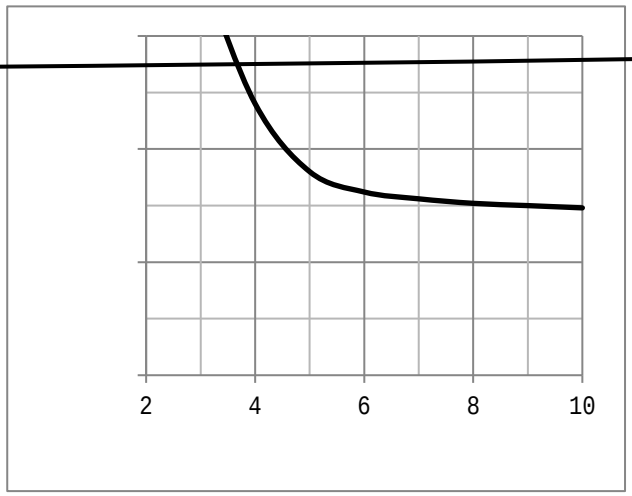

Fig.8 On-Resistance V.S Junction Temperature

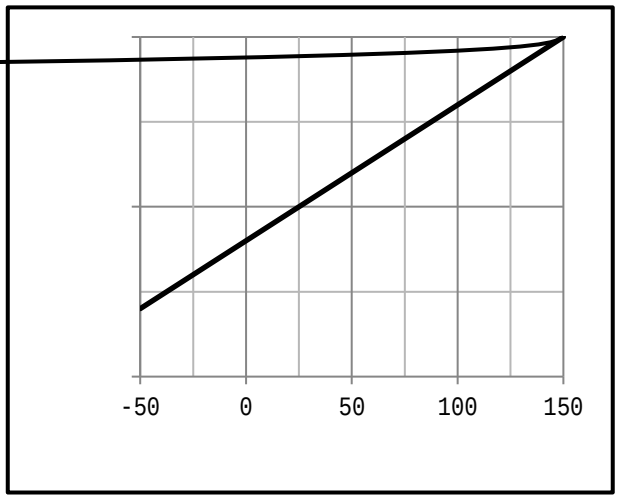

Fig.9 Switching Time Measurement Circuit

Fig.10 Gate Charge Waveform

Fig.11 Avalanche Measurement Circuit

Fig.12 Avalanche Waveform

(DFN2*2)

Unit mm